SLLS408C - JANUARY 2000 - REVISED AUGUST 2002

- Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU v.28 Standards
- Operates With 3-V to 5.5-V V_{CC} Supply
- Operates up to 250 kbit/s
- Two Drivers and Two Receivers
- Low Standby Current . . . 1 μA Typical
- External Capacitors . . . 4 × 0.1 μF
- Accepts 5-V Logic Input With 3.3-V Supply
- Designed to Be Interchangeable With Maxim MAX3222
- RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)
- Applications
 - Battery-Powered Systems, PDAs, Notebooks, Laptops, Palmtop PCs, and Hand-Held Equipment

(TOP VIEW) 20 PWRDOWN <u>EΝ</u>Γ C1+[]₂ 19 V_{CC} V+[]3 18 GND C1-[]4 17 DOUT1 C2+[]5 16 RIN1 C2-¶6 15 ROUT1 V−**П** 7 14 **∏** NC DOUT2 ¶8 13 DIN1 RIN2 9 12 | DIN2 ROUT2 10 11 **∏** NC

DB. DW. OR PW PACKAGE

NC - No internal connection

description/ordering information

The MAX3222 consists of two line drivers, two line receivers, and a dual charge-pump circuit with ± 15 -kV ESD protection pin to pin (serial-port connection pins, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The device operates at data signaling rates up to 250 kbit/s and a maximum of 30-V/ μ s driver output slew rate.

The MAX3222 can be placed in the power-down mode by setting $\overline{PWRDOWN}$ low, which draws only 1 μA from the power supply. When the device is powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled; V+ is lowered to V_{CC} , and V- is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting \overline{EN} high.

ORDERING INFORMATION

TA	PACKAGE [†]		ORDERABLE PART NUMBER	TOP-SIDE MARKING
	SOIC (DW)	Tube	MAX3222CDW	MAX3222C
−0°C to 70°C	SOIC (DVV)	Tape and reel	MAX3222CDWR	WAX3222C
-0 0 10 70 0	SSOP (DB)	Tape and reel	MAX3222CDBR	MA3222C
	TSSOP (PW)	Tape and reel	MAX3222CPWR	MA3222C
	SOIC (DW)	Tube	MAX3222IDW	MAX3222I
40°C to 95°C	SOIC (DW)	Tape and reel	MAX3222IDWR	IVIAA3222I
-40 C 10 85°C	-40°C to 85°C SSOP (DB)		MAX3222IDBR	MB3222I
	TSSOP (PW)	Tape and reel	MAX3222IPWR	MB3222I

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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Function Tables

EACH DRIVER

IN	INPUTS			
DIN	PWRDOWN	DOUT		
Х	L	Z		
L	Н	Н		
Н	Н	L		

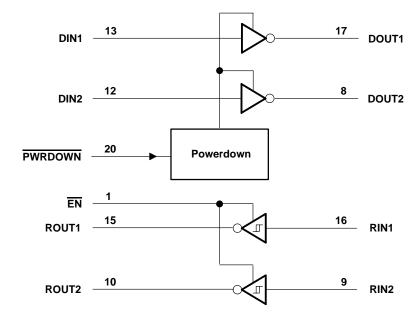
H = high level, L = low level, X = irrelevant, Z = high impedance

EACH RECEIVER

INPU	INPUTS		
RIN	EN	ROUT	
L	L	Н	
н	L	L	
Х	Н	Z	
Open	L	н	

H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = input disconnected or connected driver off

logic diagram (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC} (see Note	1)	–0.3 V to 6 V
Positive output supply voltage range,	V+ (see Note 1)	0.3 V to 7 V
Negative output supply voltage range	V- (see Note 1)	0.3 V to –7 V
Supply voltage difference, V+ - V- (se	ee Note 1)	13 V
Input voltage range, V _I : Drivers, EN, I		
Receivers .		–25 V to 25 V
Output voltage range, VO: Drivers		13.2 V to 13.2 V
Receivers		\dots -0.3 V to V _{CC} + 0.3 V
Package thermal impedance, θ_{JA} (see	e Note 2): DB package	70°C/W
-	DW package	58°C/W
	PW package	83°C/W
Lead temperature 1,6 mm (1/16 inch)	from case for 10 seconds	260°C
Storage temperature range, T _{stg}		

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.

recommended operating conditions (see Note 3 and Figure 5)

						MAX	UNIT
Our all conflictions		V _{CC} = 3.3 V		3	3.3	3.6	V
	Supply voltage	V _{CC} = 5 V		4.5	5	5.5	٧
\/	Driver and control high-level input voltage	DIN EN DWDDOWN	V _{CC} = 3.3 V	2			V
VIH	Driver and control riigh-level input voltage	DIN, EN, PWRDOWN	V _{CC} = 5 V	2.4			٧
VIL	Driver and control low-level input voltage	DIN, EN, PWRDOWN				0.8	٧
٧ı	Driver and control input voltage	DIN, EN, PWRDOWN		0		5.5	٧
٧ _I	/ _I Receiver input voltage		-25		25	V	
T _A Operating free-air temperature		MAX3222C		0		70	°C
TA	Operating nee-all temperature	MAX3222I		-40		85)

NOTE 3: Test conditions are C1–C4 = 0.1 μ F at V $_{CC}$ = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V $_{CC}$ = 5 V ± 0.5 V.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 3 and Figure 5)

PARAMETER		TEST CONDITIONS	MIN	TYP [‡]	MAX	UNIT
lı	Input leakage current (EN, PWRDOWN)			±0.01	±1	μΑ
	Supply current	No load, PWRDOWN at V _{CC}		0.3	1	mA
'cc	Supply current (powered off)	No load, PWRDOWN at GND		1	10	μΑ

[‡] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

NOTE 3: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



^{2.} The package thermal impedance is calculated in accordance with JESD 51-7.

DRIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 3 and Figure 5)

	PARAMETER	TEST CONDITIO	NS	MIN	TYP†	MAX	UNIT
Vон	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = GND	5	5.4		V
VOL	Low-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	$DIN = V_{CC}$	- 5	-5.4		V
lн	High-level input current	$V_I = V_{CC}$			±0.01	±1	μΑ
IJЦ	Low-level input current	V _I at GND			±0.01	±1	μΑ
loo	Short-circuit output current‡	V _{CC} = 3.6 V,	VO = 0 V		±35	±60	mA
los	Short-circuit output current+	V _{CC} = 5.5 V,	V _O = 0 V		±35	±00	ША
r _O	Output resistance	V_{CC} , V+, and V- = 0 V,	V _O = ±2 V	300	10M		Ω
l _{off}	Output leakage current	PWRDOWN = GND, V _{CC} = 0 to 5.5 V	$V_0 = \pm 12 \text{ V},$			±25	mA

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

NOTE 3: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 3 and Figure 5)

	PARAMETER	TEST CONDITIONS		MIN	TYP [†]	MAX	UNIT
	Maximum data rate	C _L = 1000 pF, One DOUT switching,	$R_L = 3 \text{ k}\Omega$, See Figure 1	150	250		kbit/s
t _{sk(p)}	Pulse skew§	C _L = 150 pF to 2500 pF, See Figure 2	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$		300		ns
SR(tr)	Slew rate, transition region	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$	C _L = 150 pF to 1000 pF	6		30	V/us
SK(II)	(See Figure 1)	VCC = 3.3 V	C _L = 150 pF to 2500 pF	4		30	ν/μδ

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

NOTE 3: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



^{\$} Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.

Pulse skew is defined as |tplH - tpHL| of each channel of the same device.

RECEIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 3 and Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
Vон	High-level output voltage	I _{OH} = -1 mA	V _{CC} – 0.6 V	V _{CC} – 0.1 V		V
VOL	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
\/. -	Positive-going input threshold voltage	V _{CC} = 3.3 V		1.5	2.4	V
V _{IT+}	Fositive-going input timeshold voltage	V _{CC} = 5 V		1.8	2.4	V
\/	Negative-going input threshold voltage	V _{CC} = 3.3 V	0.6	1.2		V
VIT-	Negative-going input tineshold voltage	V _{CC} = 5 V	0.8	1.5		V
V _{hys}	Input hysteresis (V _{IT+} - V _{IT-})			0.3		V
l _{off}	Output leakage current	EN = V _{CC}		±0.05	±10	μΑ
rį	Input resistance	$V_{I} = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. NOTE 3: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 3)

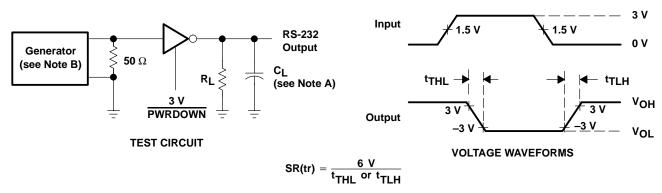
	PARAMETER	TEST CONDITIONS	MIN TYPT MAX	UNIT
^t PLH	Propagation delay time, low- to high-level output	C_{L} = 150 pF, See Figure 3	300	ns
^t PHL	Propagation delay time, high- to low-level output	C _L = 150 pF, See Figure 3	300	ns
t _{en}	Output enable time	C_L = 150 pF, R_L = 3 kΩ, See Figure 4	200	ns
^t dis	Output disable time	C_L = 150 pF, R_L = 3 kΩ, See Figure 4	200	ns
t _{sk(p)}	Pulse skew [‡]	See Figure 3	300	ns

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^{\circ}\text{C}$.

‡ Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device. NOTE 3: Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V.



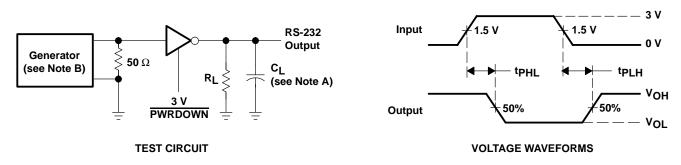
PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50~\Omega$, 50% duty cycle, $t_\Gamma \le 10$ ns. $t_f \le 10$ ns.

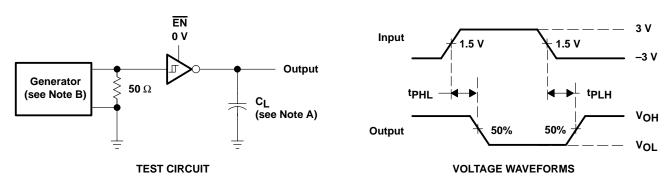
Figure 1. Driver Slew Rate



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_Q = 50 \Omega$, 50% duty cycle, $t_f \le 10$ ns. $t_f \le 10$ ns.

Figure 2. Driver Pulse Skew



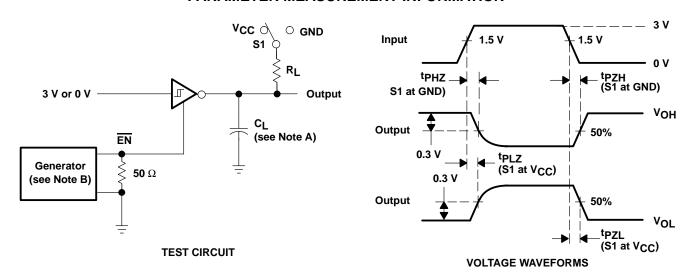
NOTES: A. C_I includes probe and jig capacitance.

B. The pulse generator has the following characteristics: $Z_O = 50 \ \Omega$, 50% duty cycle, $t_f \le 10 \ ns$, $t_f \le 10 \ ns$.

Figure 3. Receiver Propagation Delay Times



PARAMETER MEASUREMENT INFORMATION

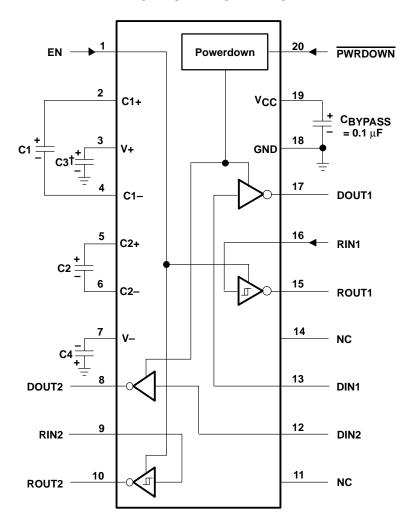


NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: $Z_O = 50~\Omega$, 50% duty cycle, $t_\Gamma \le 10~ns$, $t_f \le 10~ns$.

Figure 4. Receiver Enable and Disable Times

APPLICATION INFORMATION



 † C3 can be connected to VCC or GND. NOTES: A. Resistor values shown are nominal.

B. NC – No internal connection.

V_{CC} vs CAPACITOR VALUES

VCC	C1	C2, C3, and C4
3.3 V \pm 0.3 V	0.1 μ F	0.1 μ F
5 V ± 0.5 V	0.047 μ F	0.33 μ F
3 V to 5.5 V	0.1 μ F	0.47 μ F

Figure 5. Typical Operating Circuit and Capacitor Values



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